

FIG. 1

10040027-102501

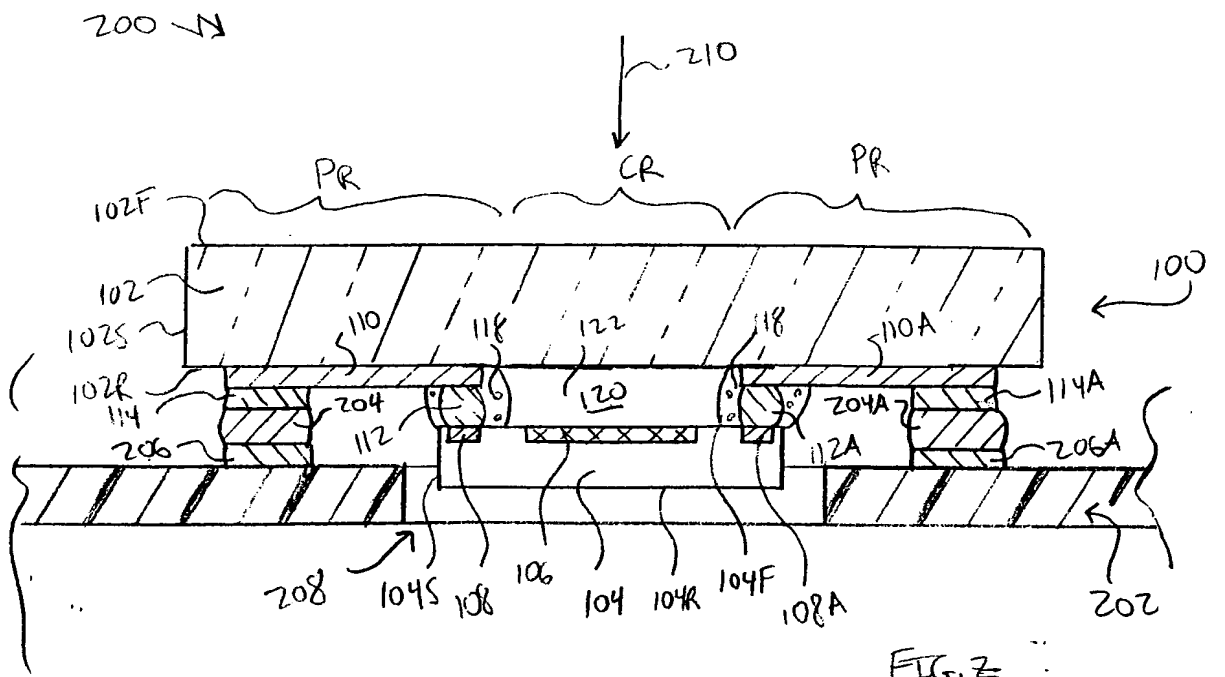


FIG. 2

300 ↘

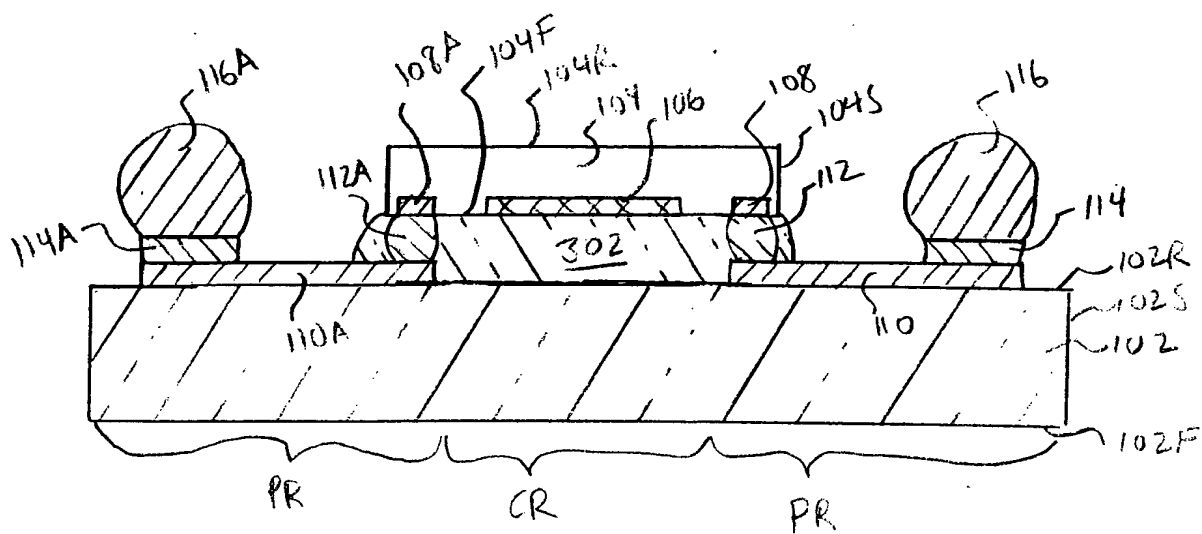
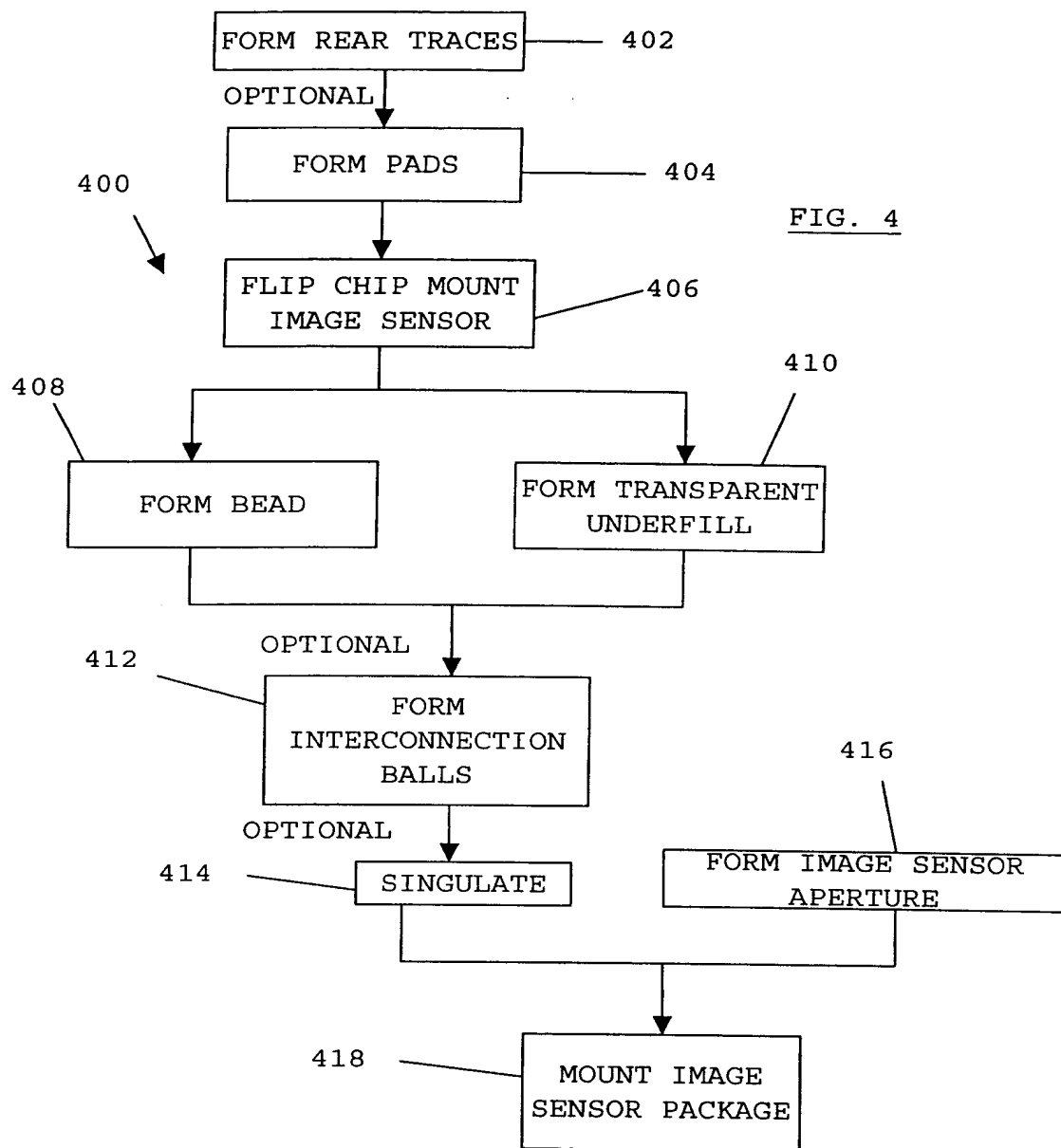


FIG. 3



10040027-102600

500 ↘

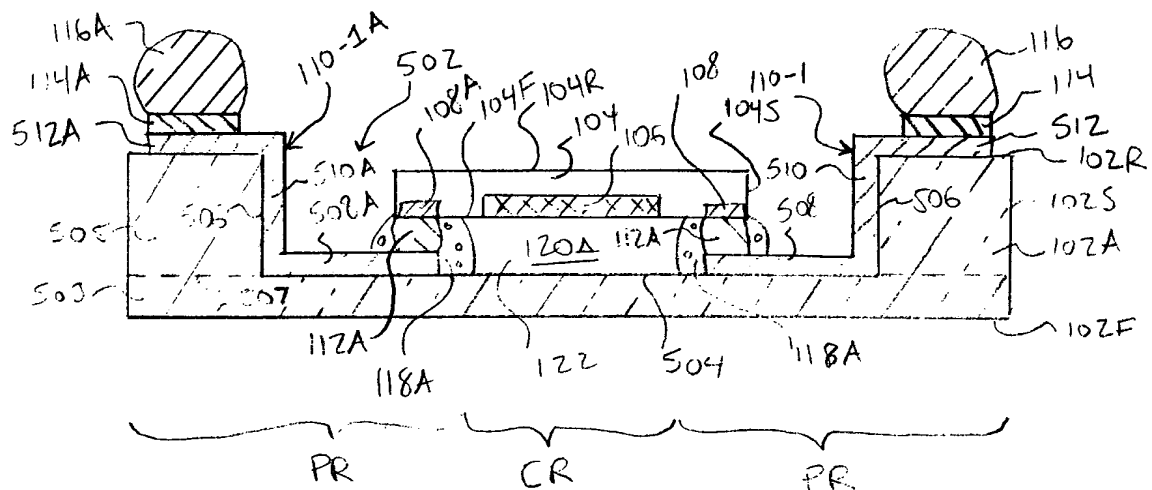


FIG. 5

10040027-102501

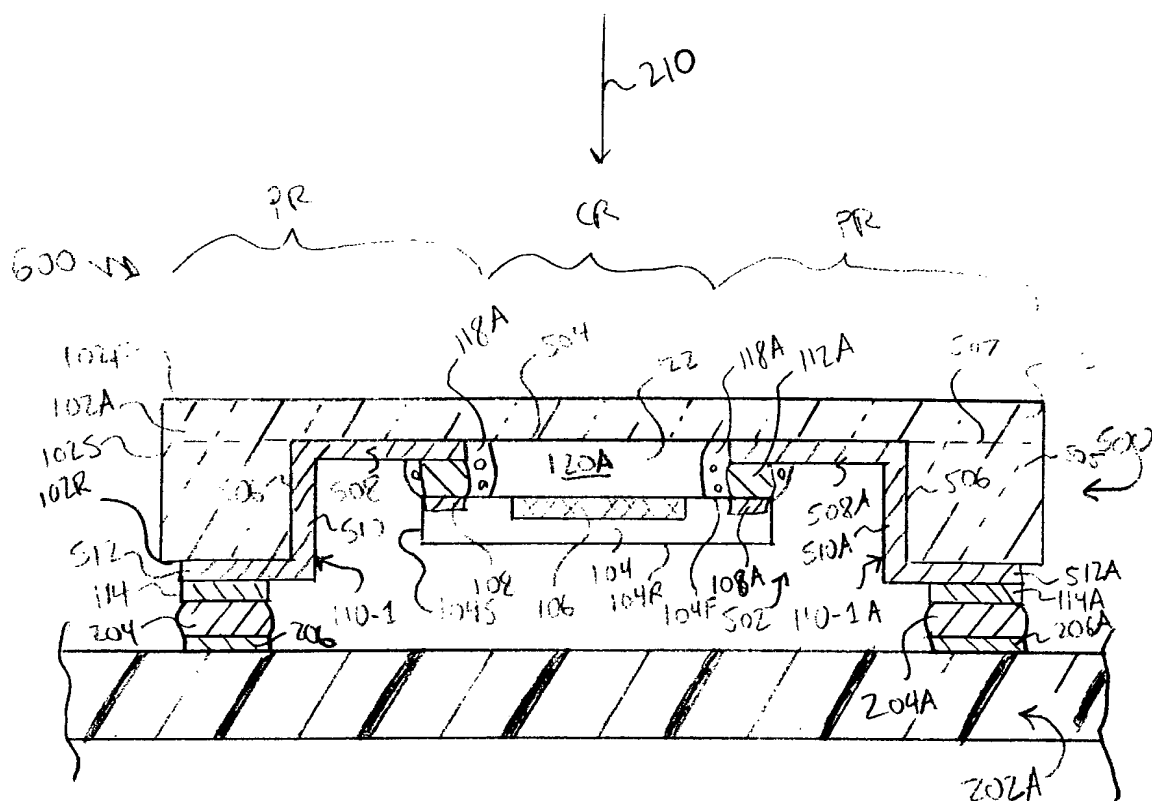
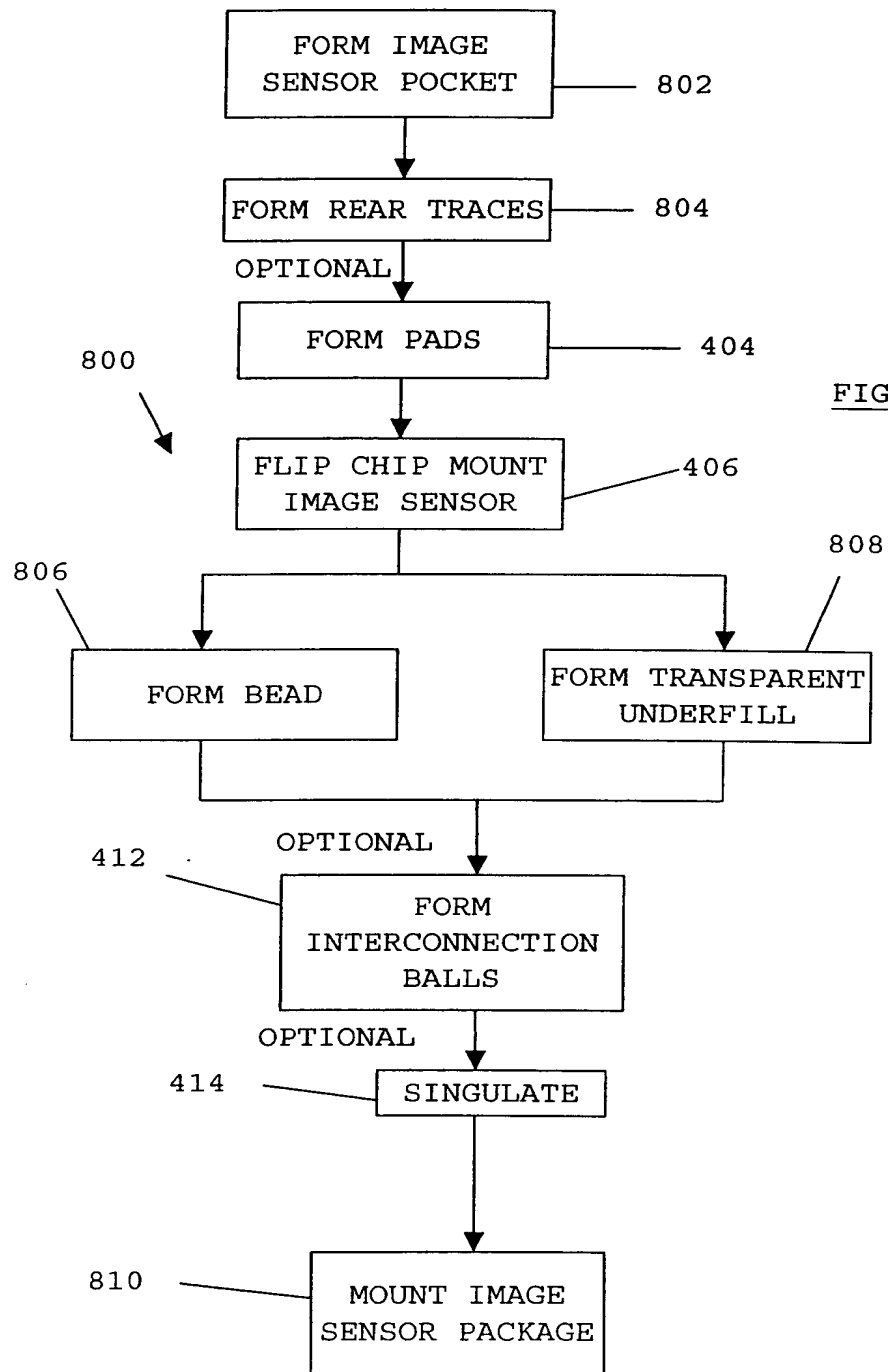


FIG. 6

A cross-sectional view of a semiconductor device. The device features a central core region (CR) flanked by two peripheral regions (PR). The PR regions are defined by a patterned layer 110-1A, which is part of a larger structure 110-1. The CR region is defined by a patterned layer 110-1B. The device includes a substrate 102, a base layer 104, and a top layer 106. A central layer 108 is present in the CR region. The PR regions contain a layer 104R. The device is capped with a layer 114, which is part of a larger structure 116. The PR regions are also labeled 112A and 112B. The CR region is labeled 112A. The device is shown in a cross-sectional view, with various layers and regions labeled with reference numerals.

FIG. 7





900 ↘

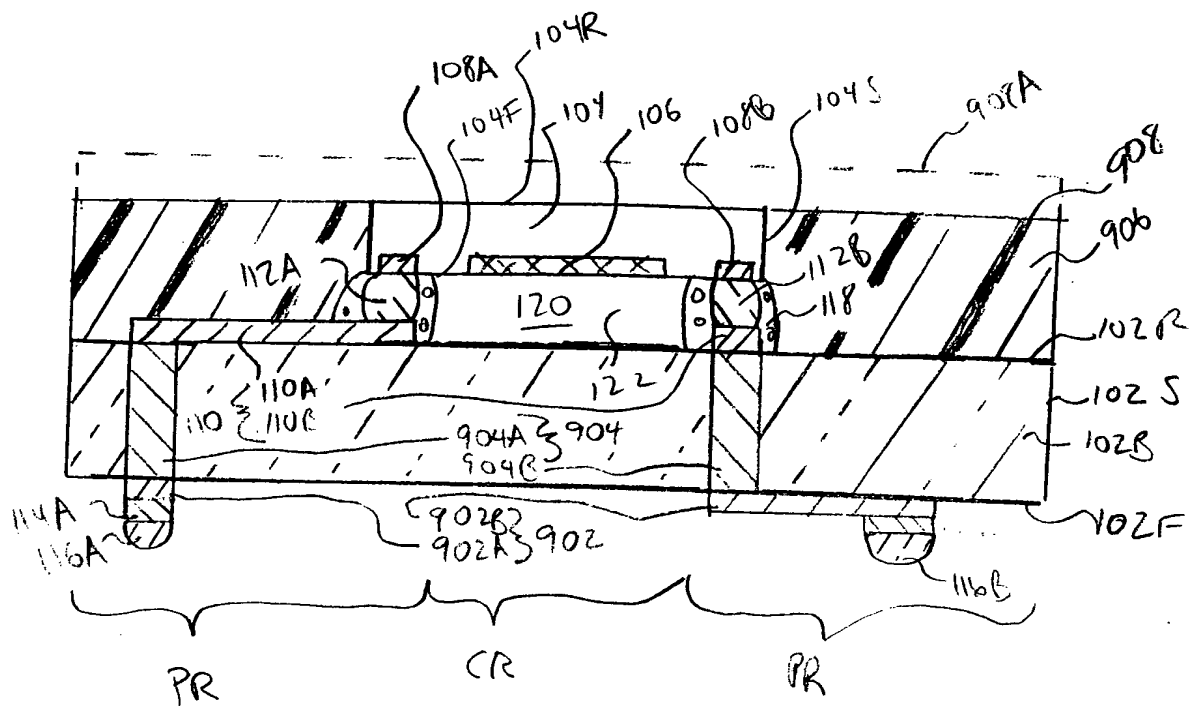


FIG. 9

10040027-102501

30440027 102501

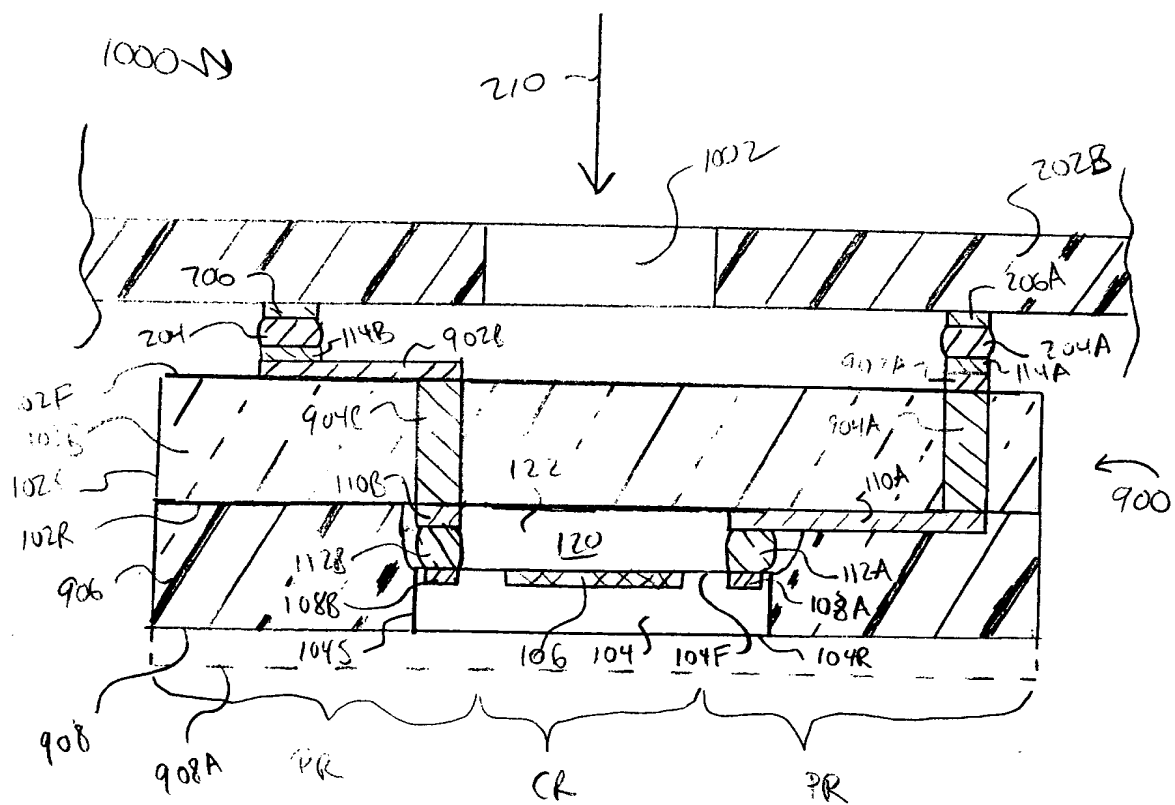


FIG. 10

FIG. 10

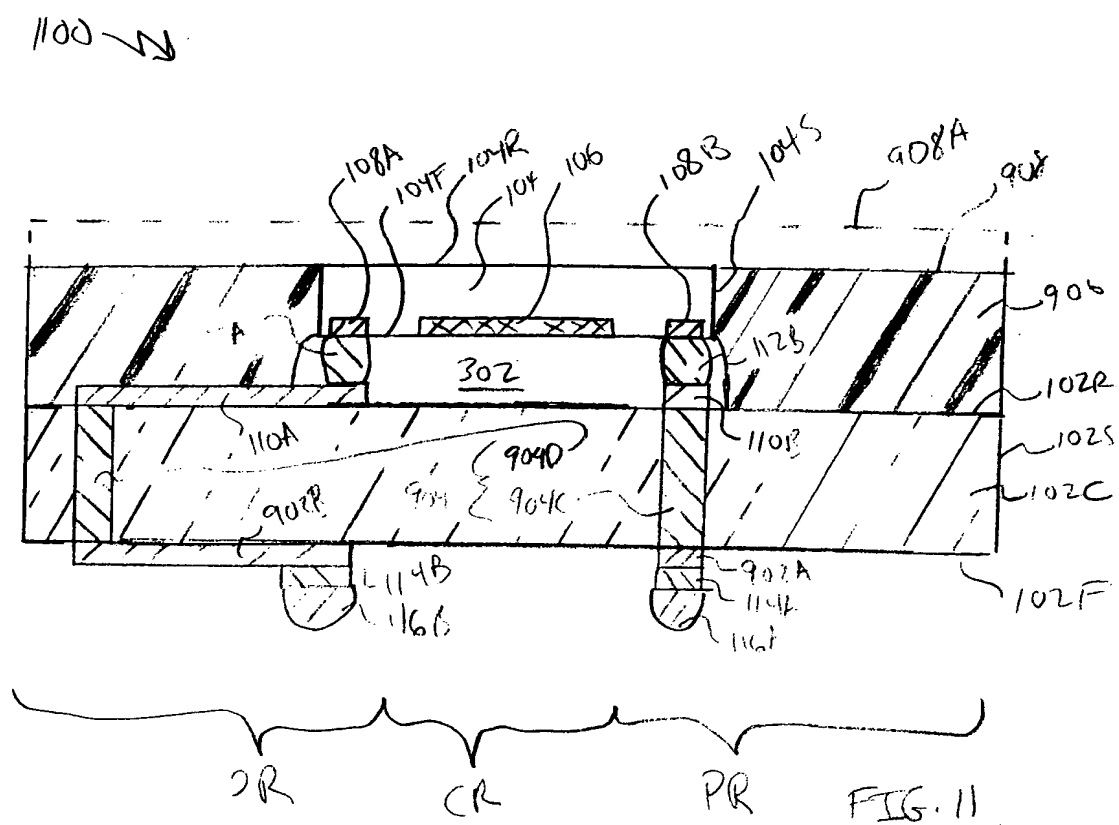


FIG. 12

